



PSMN8R2-80YS

N-channel LFPAK 80 V 8.5 m Ω standard level MOSFET

Rev. 01 — 25 June 2009

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

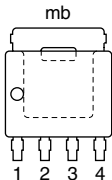
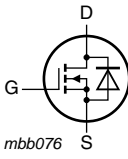
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|---|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 80 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; see Figure 1 | - | - | 82 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see Figure 2 | - | - | 130 | W |
| T _j | junction temperature | | -55 | - | 175 | °C |
| Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 75 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω ; unclamped | - | - | 120 | mJ |
| Dynamic characteristics | | | | | | |
| Q _{GD} | gate-drain charge | V _{GS} = 10 V; I _D = 25 A; | - | 12 | - | nC |
| Q _{G(tot)} | total gate charge | V _{DS} = 40 V; see Figure 14 ; see Figure 15 | - | 55 | - | nC |

Table 1. Quick reference ...continued

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|-------------------------------------|--|-----|-----|------|------|
| Static characteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 15\text{ A};$ $T_j = 100\text{ °C};$ see Figure 12 | - | - | 13.4 | mΩ |
| | | $V_{GS} = 10\text{ V}; I_D = 15\text{ A};$ $T_j = 25\text{ °C};$ see Figure 13 ; see Figure 12 | - | 5.8 | 8.5 | mΩ |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|---|
| 1 | S | source |  <p>SOT669 (LPAK)</p> |  <p>mbb076</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

3. Ordering information

Table 3. Ordering information

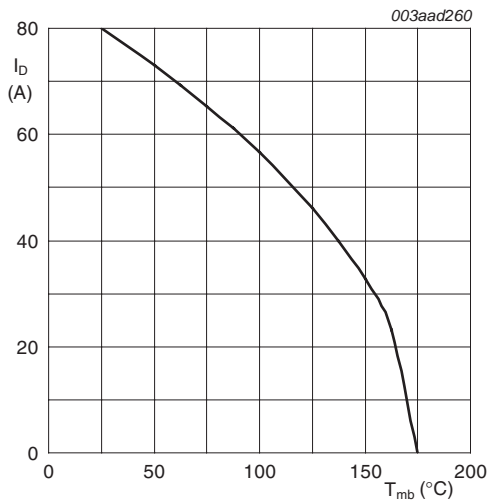
| Type number | Package | | Version |
|--------------|---------|--|---------|
| | Name | Description | |
| PSMN8R2-80YS | LPAK | plastic single-ended surface-mounted package (LPAK); 4 leads | SOT669 |

4. Limiting values

Table 4. Limiting values

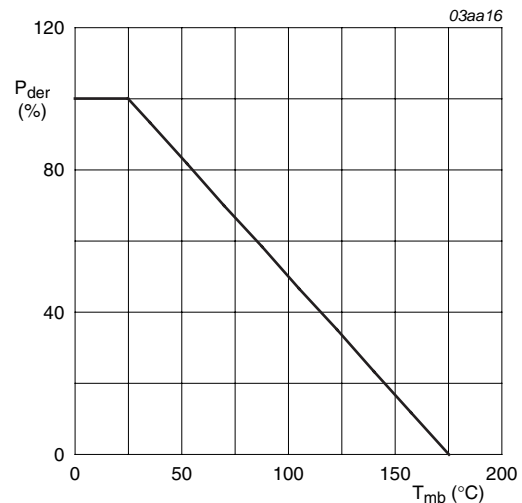
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|--|---|-----|-----|------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$ | - | 80 | V |
| V_{DGR} | drain-gate voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 80 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1 | - | 57 | A |
| | | $V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 | - | 82 | A |
| I_{DM} | peak drain current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3 | - | 326 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; see Figure 2 | - | 130 | W |
| T_{stg} | storage temperature | | -55 | 175 | °C |
| T_j | junction temperature | | -55 | 175 | °C |
| $T_{slid(M)}$ | peak soldering temperature | | - | 260 | °C |
| Source-drain diode | | | | | |
| I_S | source current | $T_{mb} = 25\text{ °C}$ | - | 82 | A |
| I_{SM} | peak source current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$ | - | 326 | A |
| Avalanche ruggedness | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 75\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped | - | 120 | mJ |



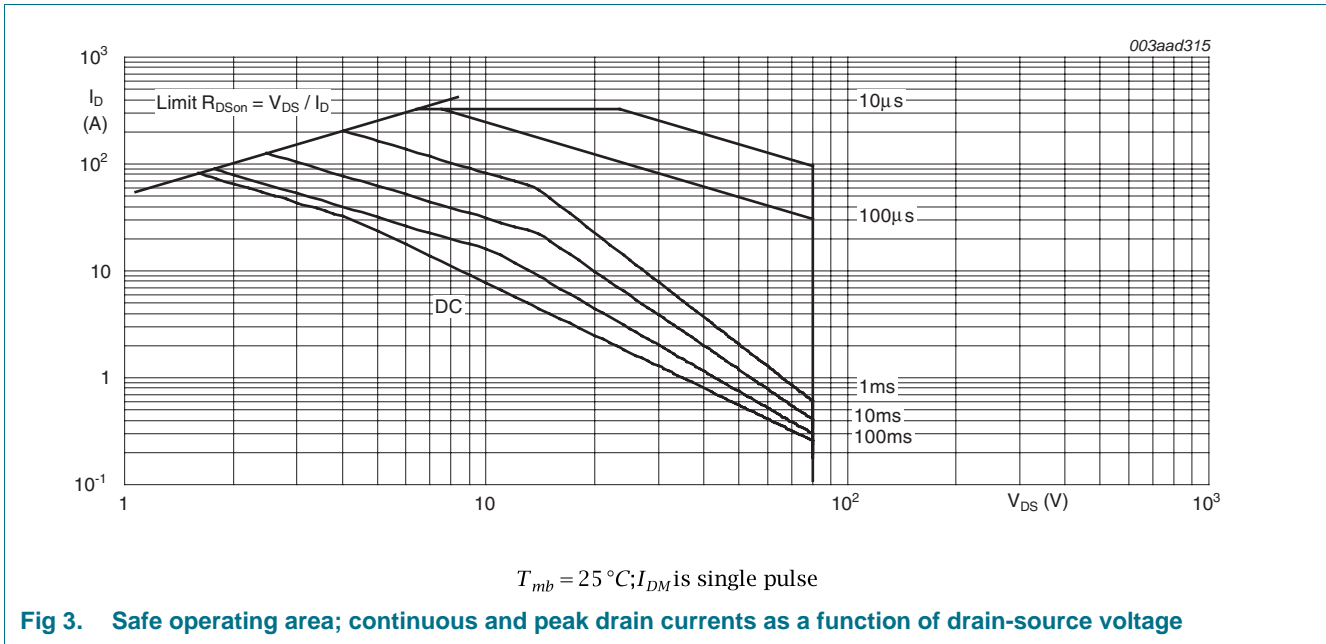
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

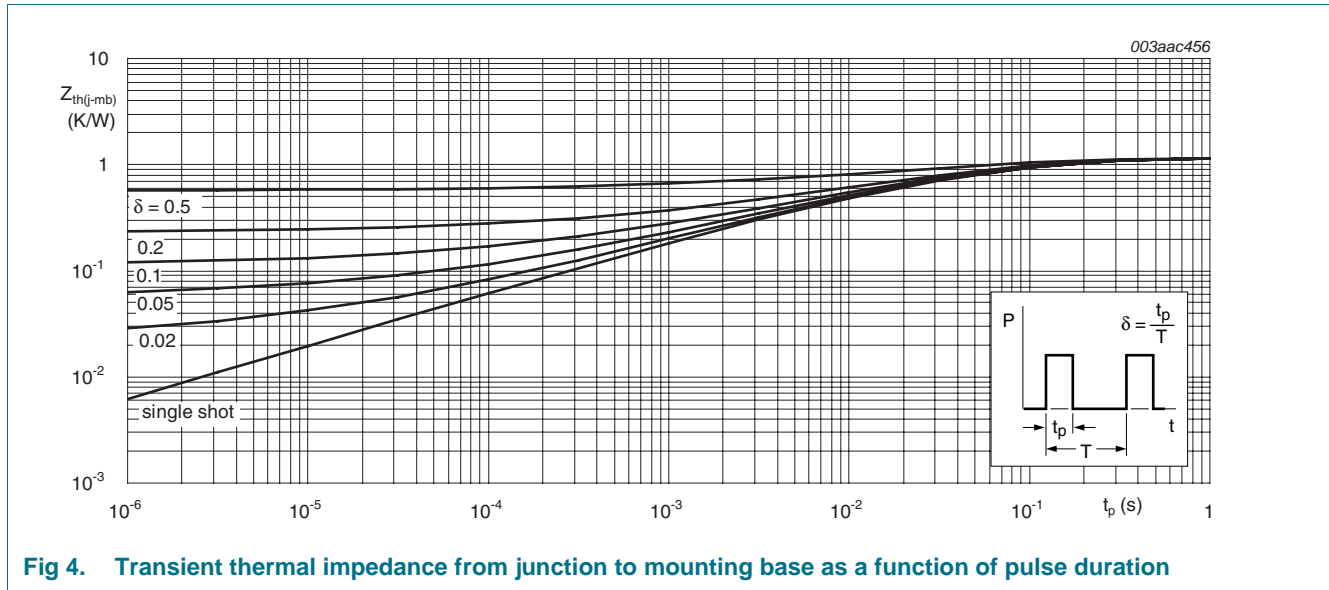
Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | - | 1.1 | K/W |



6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|--|-----|------|------|---------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ | 73 | - | - | V |
| | | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 80 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | - | - | 4.6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 2 | 3 | 4 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 4 | μA |
| | | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$ | - | - | 50 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 100 | nA |
| | | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12 | - | - | 20 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see Figure 12 | - | - | 13.4 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 13 ; see Figure 12 | - | 5.8 | 8.5 | mΩ |
| R_G | internal gate resistance (AC) | $f = 1 \text{ MHz}$ | - | 0.74 | - | Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 48 | - | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15 | - | 55 | - | nC |
| Q_{GS} | gate-source charge | | - | 15 | - | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 | - | 10 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | - | 5 | - | nC |
| Q_{GD} | gate-drain charge | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15 | - | 12 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$ see Figure 15 ; see Figure 14 | - | 4.5 | - | V |
| C_{iss} | input capacitance | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16 | - | 3640 | - | pF |
| C_{oss} | output capacitance | | - | 390 | - | pF |
| C_{rss} | reverse transfer capacitance | | - | 180 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 40 \text{ V}; R_L = 1.6 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 4.7 \text{ } \Omega$ | - | 25 | - | ns |
| t_r | rise time | | - | 22 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 51 | - | ns |
| t_f | fall time | | - | 16 | - | ns |

Table 6. Characteristics ...continued

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|-----------------------|---|-----|------|-----|------|
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; see Figure 17 | - | 0.81 | 1.2 | V |
| t_{rr} | reverse recovery time | $I_S = 50\text{ A}$; $di_S/dt = 100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; | - | 55 | - | ns |
| Q_r | recovered charge | $V_{DS} = 40\text{ V}$ | - | 106 | - | nC |

[1] Tested to JEDEC standards where applicable.

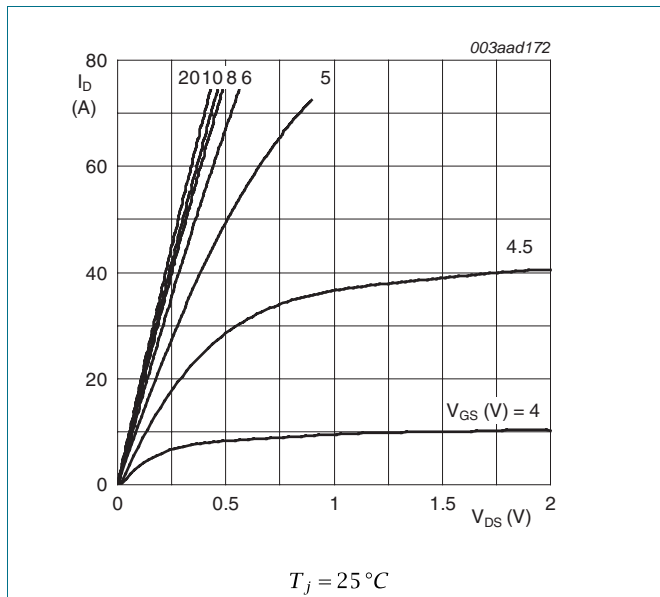


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

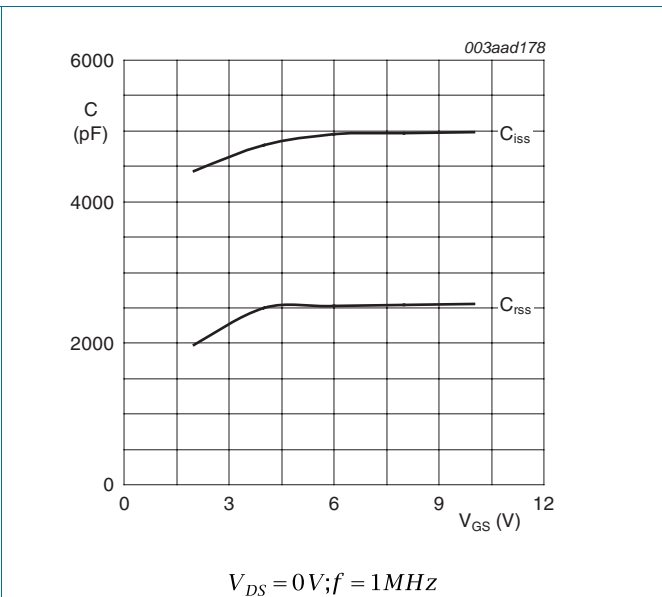


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

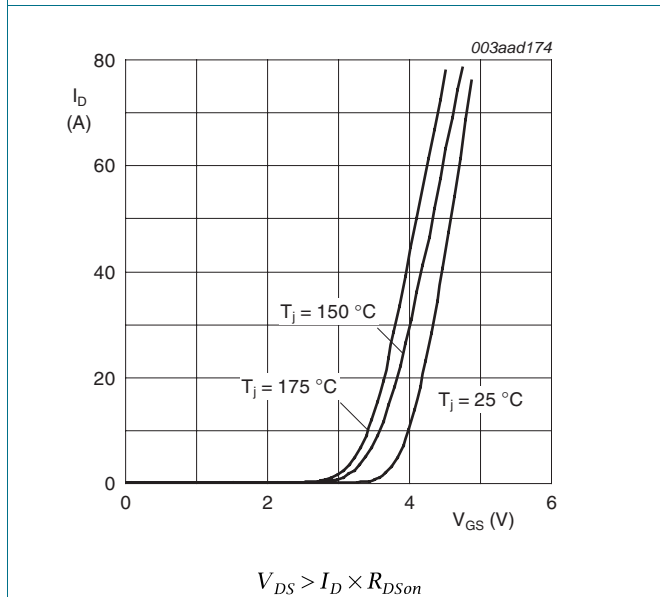


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

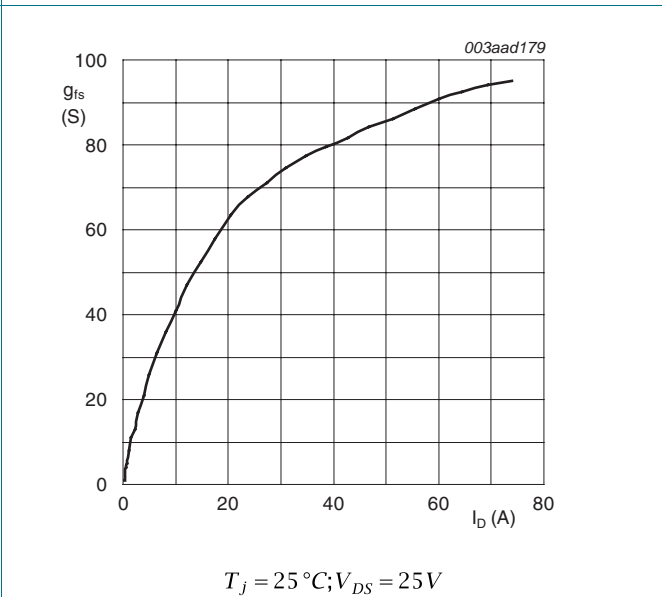
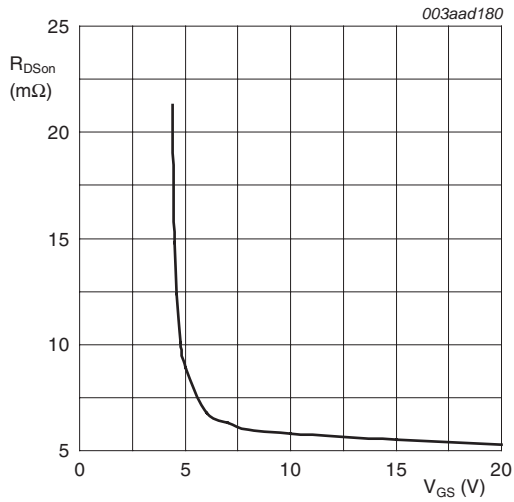
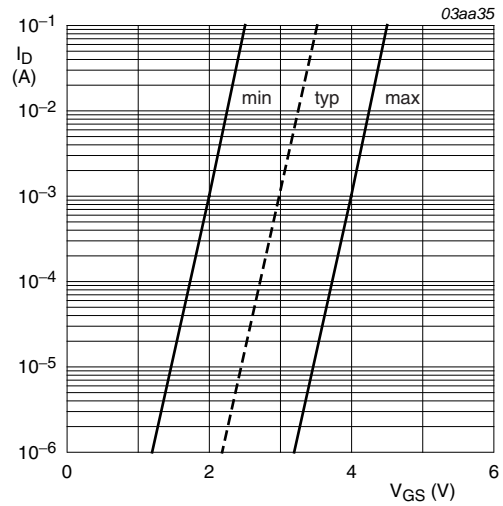


Fig 8. Forward transconductance as a function of drain current; typical values



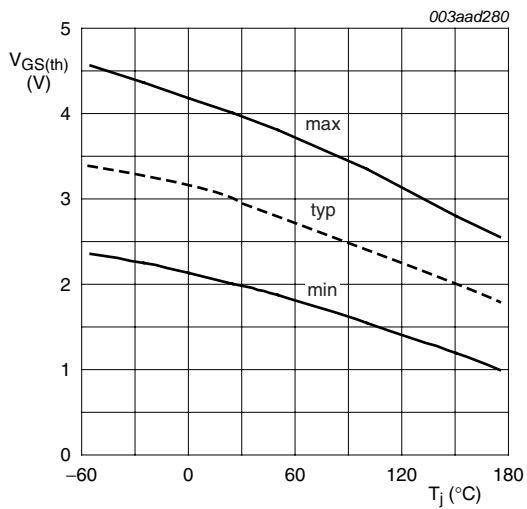
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



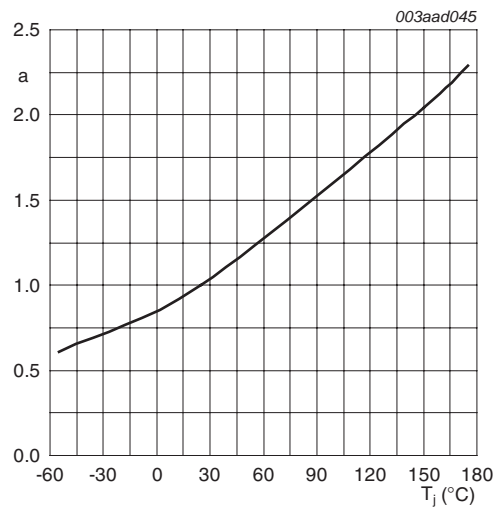
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



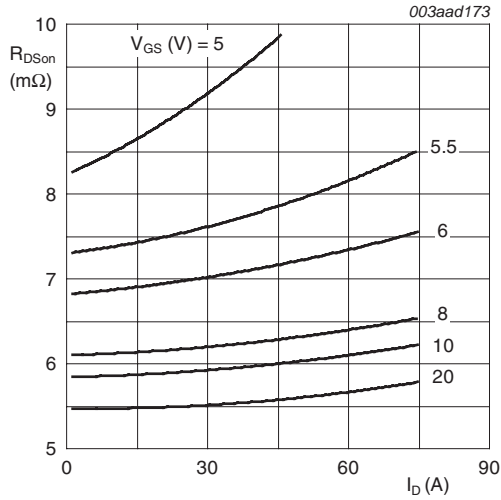
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25^\circ C$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

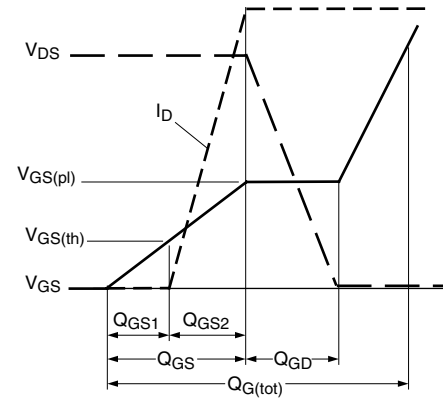
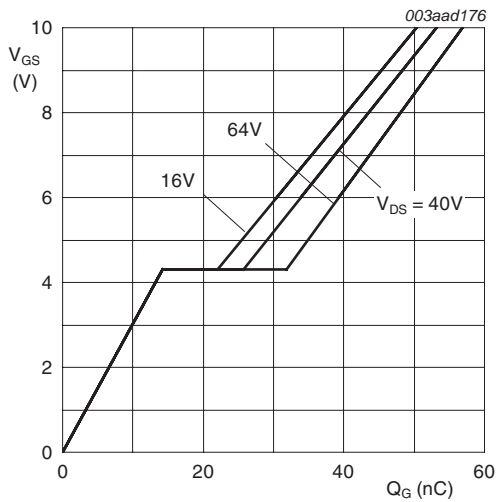
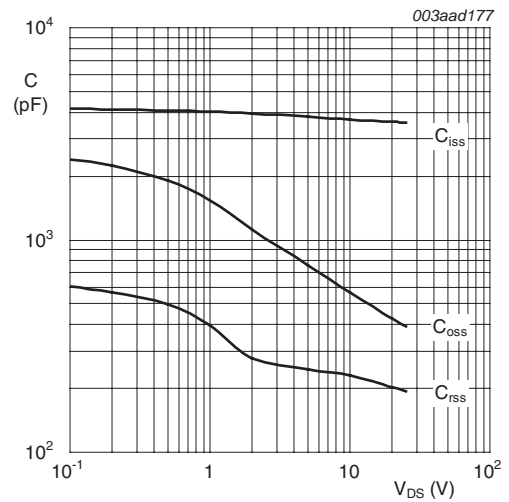


Fig 14. Gate charge waveform definitions



$T_j = 25^\circ C; I_D = 25 A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 V; f = 1 MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

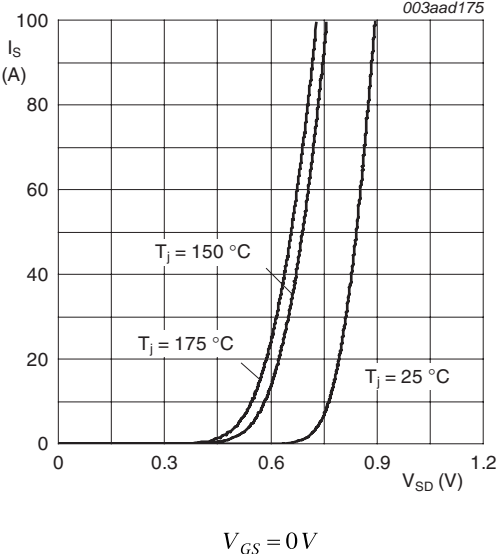


Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

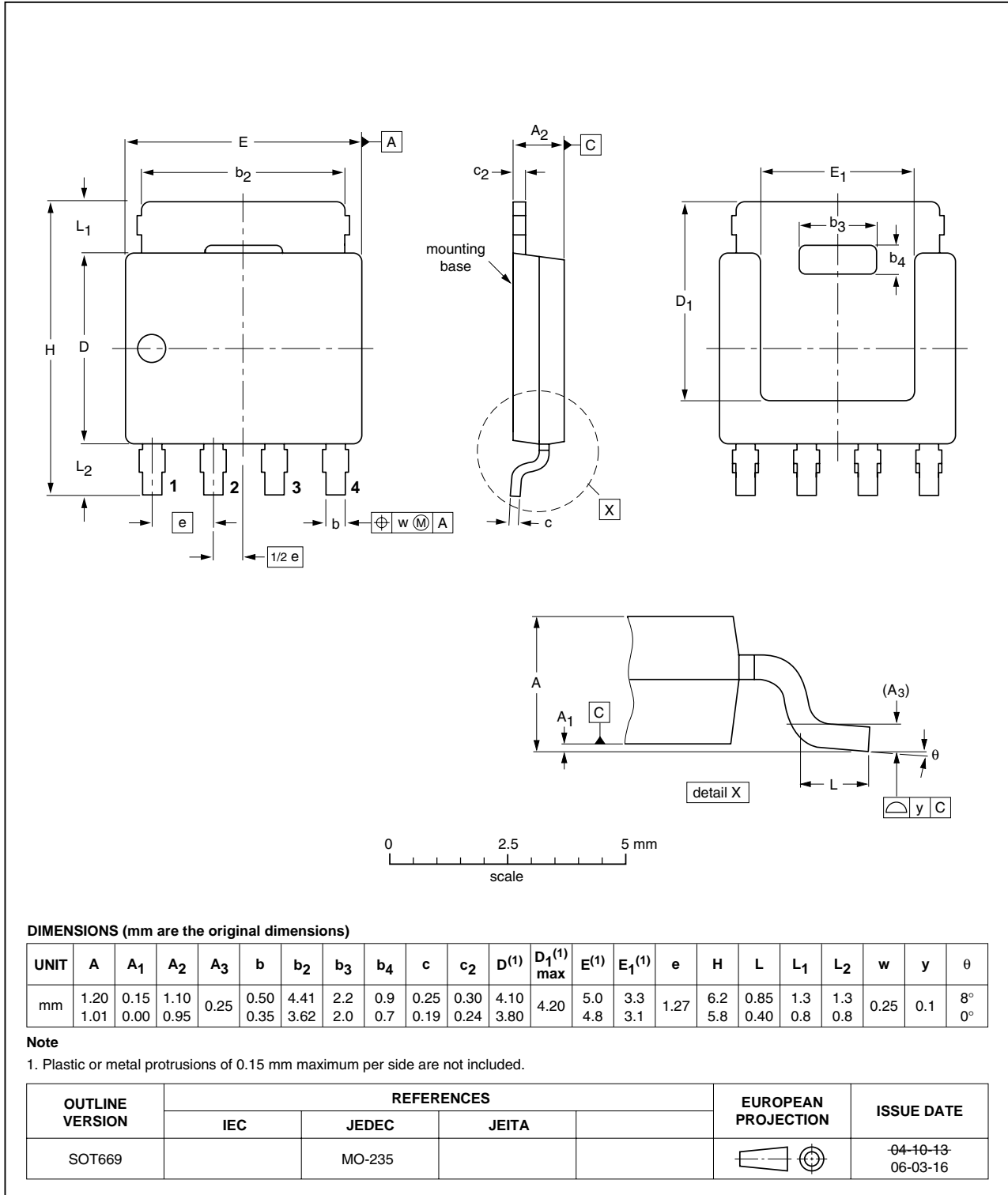


Fig 18. Package outline SOT669 (LPAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|--------------|--------------|--------------------|---------------|------------|
| PSMN8R2-80YS | 20090625 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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